

FDP5645/FDB5645

60V N-Channel PowerTrench® MOSFET

General Description

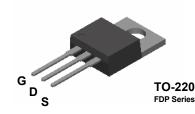
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\rm DS(ON)}$ specifications.

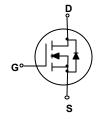
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 80 A, 60 V. $\begin{aligned} R_{_{DS(ON)}} &= 0.0095 \; \Omega \; @ \; V_{_{GS}} = 10 \; V \\ R_{_{DS(ON)}} &= 0.011 \; \Omega \; @ \; V_{_{GS}} = 6 \; V. \end{aligned}$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low $R_{\scriptscriptstyle DS/(\rm ON)}.$
- 175°C maximum junction temperature rating.







S TO-263AB FDB Series

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	FDP5645 FDB5645	Units
V _{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	±20	V
l _D	Maximum Drain Current — Continuous (note 3)	80	Α
	– Pulsed	300	
P _D	Total Power Dissipation @ T _C = 25°C	125	W
	Derate above 25°C	0.83	W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C
TL	Maximum lead termperature for soldering purposes, 1/8" from case for 5 seconds	+275	°C

Thermal Characteristics

R _{eJC}	Thermal Resistance, Junction-to-Case	1.2	°C/W
Baia	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB5645	FDB5645	13"	24mm	800 units
FDP5645	FDP5645	note 2		

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note 1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 40 \text{ V}, \qquad I_D = 80 \text{ A}$			800	mJ
l _{AR}	Maximum Drain-Source Avalanche Current				80	А
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
<u>ΔBV DSS</u> ΔTJ	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		64		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
	acteristics (Note 1)	,		ı	1	1
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{CS}$, $I_D = 250 \mu A$	2		4	V
ΔV GS(th) $\Delta T_{ m J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-7.8		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		8 13 9	9.5 18 11	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g FS	Forward Transconductance	$V_{DS} = 5 V$, $I_D = 40 A$		88		S
Dvnamio	: Characteristics					
Ciss	Input Capacitance	$V_{DS} = 30 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		4468		pF
Coss	Output Capacitance	f = 1.0 MHz		810		pF
C _{rss}	Reverse Transfer Capacitance			198		pF
Switchin	g Characteristics (Note 2)			I		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, \qquad I_D = 1 \text{ A},$		21	30	ns
t _r	Turn–On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	20	ns
t _{d(off)}	Turn-Off Delay Time	1		77	90	ns
t _f	Turn-Off Fall Time	1		42	50	ns
Qq	Total Gate Charge	$V_{DS} = 30 \text{ V}, \qquad I_D = 80 \text{ A},$		76	107	nC
Qgs	Gate–Source Charge	$V_{GS} = 10 \text{ V}$		18	_	nC
Q _{ad}	Gate-Drain Charge			21		nC
	ource Diode Characteristics a	and Maximum Patings		I	<u>I</u>	<u>I</u>
ls	Maximum Continuous Drain–Source				80	Α
ls .	Maximum Pulsed Drain–Source Diod				300	A
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 40 \text{ A}$		0.9	1.3	V

Notes

- 1. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%
- 2. TO-220 package is supplied in tube / rail @ 45 pieces per rail.
- 3. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A

Typical Characteristics

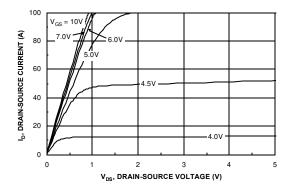


Figure 1. On-Region Characteristics.

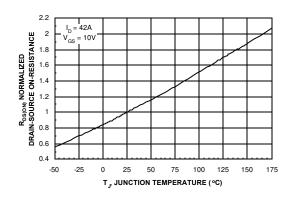


Figure 3. On-Resistance Variation withTemperature.

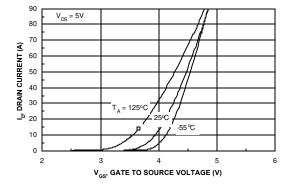


Figure 5. Transfer Characteristics.

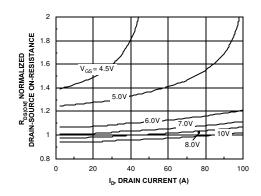


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

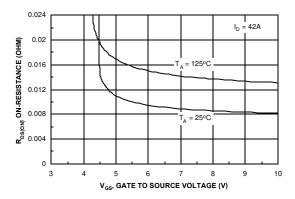


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

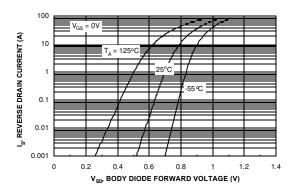
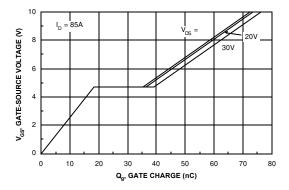


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



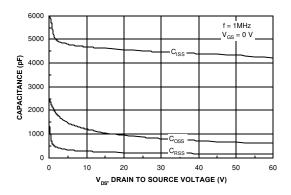


Figure 7. Gate Charge Characteristics.

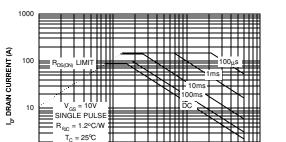


Figure 8. Capacitance Characteristics.

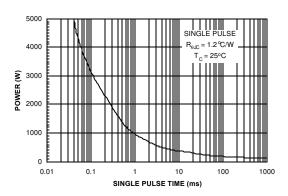


Figure 9. Maximum Safe Operating Area.

V_{DS'} DRAIN-SOURCE VOLTAGE (V)

0.1



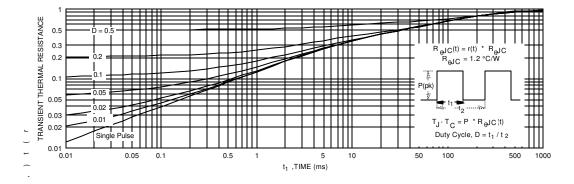
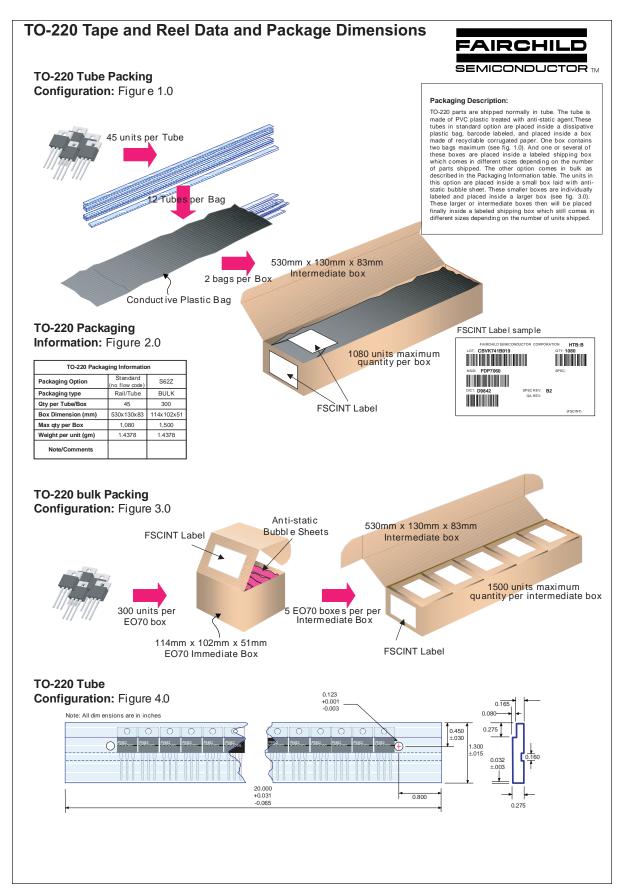


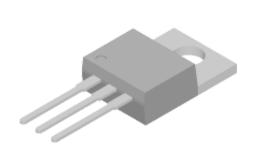
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

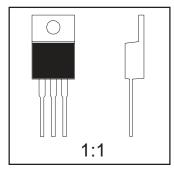


TO-220 Tape and Reel Data and Package Dimensions, continued

TO-220 (FS PKG Code 37)

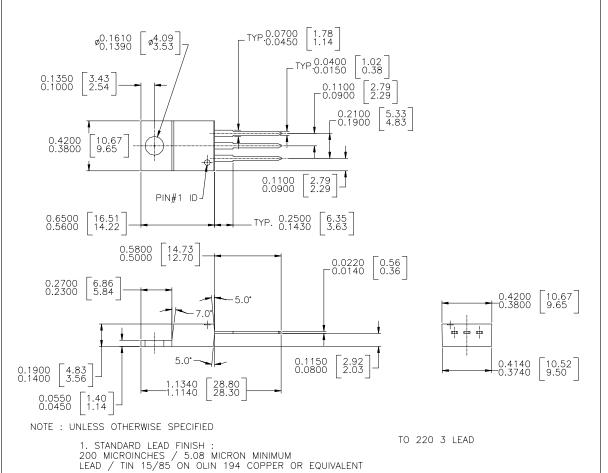


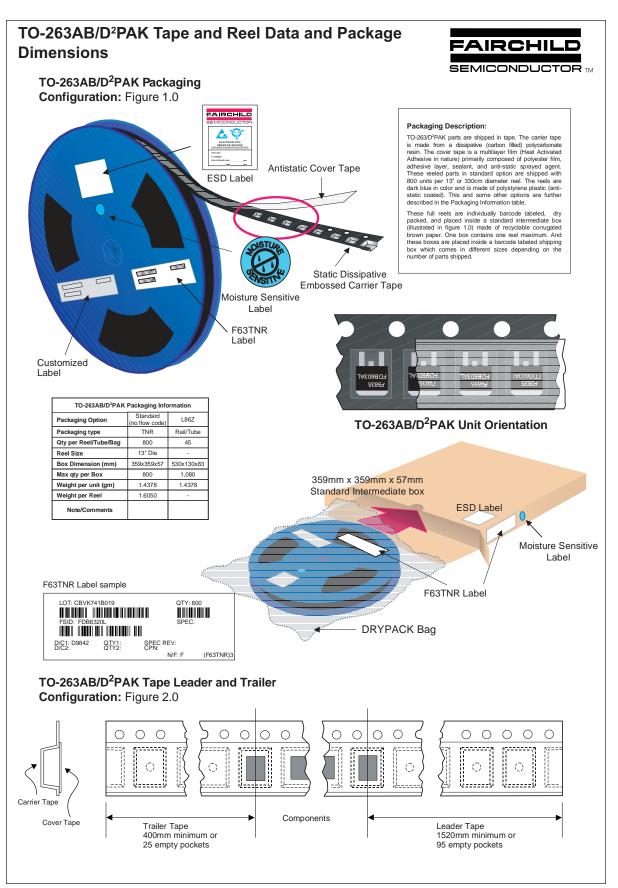
2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

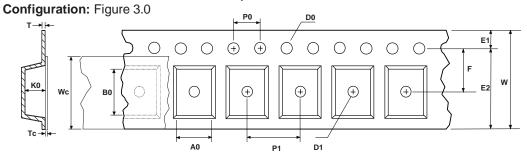
Part Weight per unit (gram): 1.4378





TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



User Direction of Feed

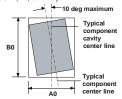
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D ² PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation



Sketch B (Top View)
Component Rotation

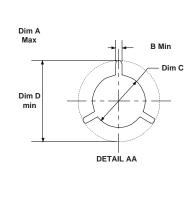
W1 Measured at Hub



Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0





13" Diameter Option

W2 max Measured at Hub

Dim N

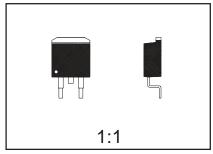
See detail AA

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

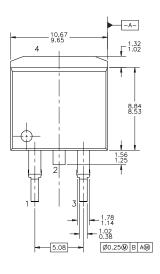
TO-263AB/D²PAK (FS PKG Code 45)

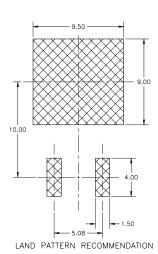


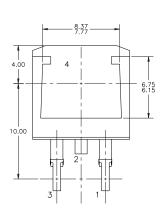


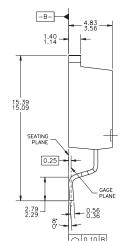
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—265, ISSUE C,
 VARIATION AB, DATED 2/92.

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Datasheet Identification	Product Status	Definition			
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